

GaAs substrate





# Graphene and its conductivity

- Resonance condition:  $L = \frac{\lambda_{SPP}}{2} = \frac{\pi}{k_{SPP}}$
- Plasmon dispersion relation:  $\frac{1}{\sqrt{k_{SPP}^2 \frac{\omega^2}{c^2}}} + \frac{\varepsilon}{\sqrt{k_{SPP}^2 \varepsilon\frac{\omega^2}{c^2}}}$



Anwar, et al. Digital Communications and Networks, 2018. 4(4), 244-257.

#### Chemical potential $(\mu_c)$

Tuned by bias voltage or doping

 $\frac{\sigma(\omega\mu_{c}\tau)}{\omega\epsilon_{0}}$ 

- Determines number of n & p in antenna
   Relaxation time (τ)
- Average life time of charges
- Determined by graphene quality

For functional antenna  $\rightarrow$  large  $\mu_c \& \tau$ 

→ Challenge: high-quality graphene!

#### Structure of THz Antenna







#### **Dipole antenna**

- GaAs substrate (E<sub>g</sub> = 1.42 eV)
- Conduction lines & contact: Cr / Au
- Two graphene patches

- Supports SPPs in THz band (0.1 10 THz)
- Graphene SPP waves tuned by doping
- Design/shape of graphene antennas

# Mechanical exfoliation

#### Advantages

- Monocrystalline Graphene
- Defect-free
- $\rightarrow$  Cleanliness, high conductivity

#### Challenges

- Low yield
- Non-deterministic
- Small and irregular flakes

#### Parameters:

- Graphite source
- Tape (Nitto, Tesa)
- Force, speed, direction applied
- Number of subsequent exfoliations



Freire Soler, Doctoral dissertation, 2014.



https://lmn.mb.uni-siegen.de/

## Challenges of mechanical exfoliation



- Multiple subsequent exfoliations
- 100 °C for 1 min
- → Small, irregular & thick flakes

Challenge  $\rightarrow$  Residue removal

## Tape residue removal



- 10 min in acetone
- Blow dried with N<sub>2</sub>
- $\rightarrow$  Cleaner surface & flakes remain

## Exfoliation of large area graphene flakes





- Less number of subsequent exfoliations
- 75 °C for 3 min
- $\rightarrow$  Clean, thin & bigger flakes

## Thickness determination using contrast spectra

- Model based on the Fresnel law
- White light source and no filter



#### Contrast of graphene on SiO<sub>2</sub>/Si



## Thickness determination using contrast spectra

Intensities with ImageJ

#### **Contrast equation**

$$C = \frac{I(n_1 = 1) - I(n_1)}{I(n_1 = 1)}$$

#### **Number of layers**

 $C = 0.0046 + 0.0925N - 0.00255N^2$ 



Ni, et al. Nano letters, 2007, 7(9), 2758-2763.

#### Raman spectroscopy



- No D peak (1350 cm<sup>-1</sup>)
- G' band single Lorentzian profile
- FWHM 22.3 cm<sup>-1</sup>
- *I<sub>G</sub>/I<sub>G</sub>′* (0.37)
- $\rightarrow$  Typical values for defect-free, ME graphene



- 532 nm laser
- 1200 l/mm grating
- 600 nm center wavelength

## All-dry transfer method: Transfer tool









## Pick up technique of flakes









# Pick up technique of flakes

Selection of graphene on SiO<sub>2</sub>/Si substrate



#### Challenges

- PC coating would break
- PDMS sticked to the substrate
- $\rightarrow$  Parameter optimization



iii. Pick-up



Pizzocchero, et al. Nature communications, 2016, 7(1), 1-10.

## Visibility of graphene/graphite on GaAs substrate

Flake on antenna (	Transfer OM)	Thin flake on PDMS
	1601.66 Sample Si-GR01 Fitted plot	<u>100 μm</u>
2 <u>00 μm</u> High contrast at contact with Au	<sup>2459.17</sup> 1400 1600 1800 2000 2200 2400 2600 2800 Raman shifts/ cm <sup>-1</sup>	Flake on antenna (Transfer OM)
Glass slide PDMS Flake T0°C SiO <sub>2</sub>	<ul> <li>Extremely low contrast on GaAs</li> <li>Raman measurements required</li> </ul>	<u>50 μm</u>

#### Outlook





- Raman spectroscopy mapping
- Rapid optical thickness using contrast
- Correlation of contrast and thickness on GaAs
- Complimentary techniques (AFM)
- Correlation of contrast and thickness on PDMS



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